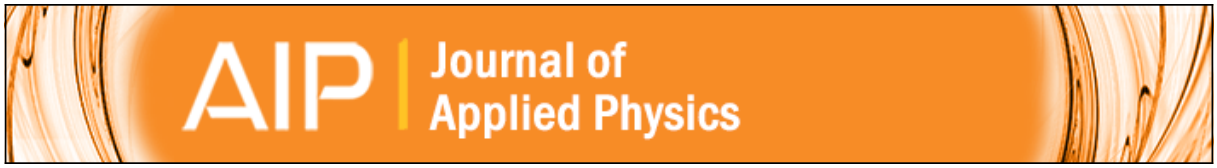

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Hong-Wen Hsieh and Shun-Tung Yen

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Erratum: "Analysis of GaAs/GaSb/GaAs structures under optical excitation considering surface states as an electron reservoir" [J. Appl. Phys. 105, 103515 (2009)]

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In the paper, Fig. 5 should be corrected as follows.

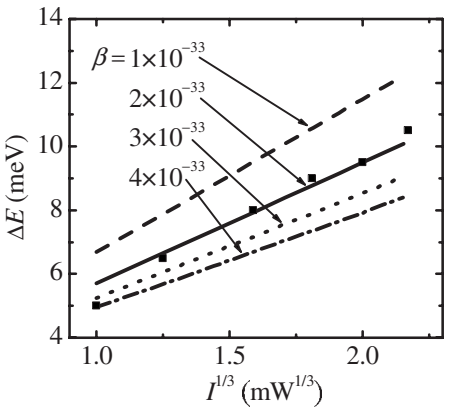

FIG. 5. The calculated energy difference ΔE as a function of the cube root of excitation power, $I^{1/3}$, with β as a parameter (in $\mathrm{mW \cdot cm^6}$). Also shown are the experimental data (denoted by the filled squares) which are obtained by shifting the data of Ref. 3 by a common energy for the structure with a 2 ML GaSb layer. They give a slope $d\Delta E/dI^{1/3} \approx 4.1\ \mathrm{meV/mW^{1/3}}$, corresponding to $\beta \approx 2 \times 10^{-33}\ \mathrm{mW \cdot cm^6}$.

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